

## ABSTRACT OF THE DISCLOSURE

The present invention provides a method of treating a surface of  
5 a semiconductor substrate, the surface of the semiconductor substrate  
including at least any one of a copper region, a copper based region and a  
copper alloy region, the method comprises the steps of : carrying out an  
anti-corrosion treatment by exposing the surface of the semiconductor  
10 substrate to a solution containing an anti-corrosive agent ; and forming a  
copper-diffusion stopper insulating film over the surface of the  
semiconductor substrate.